

AMENDMENTS TO THE CLAIMS

Please amend allowable claim 2 with the subject matter of its base claim 1, cancel claim 1 without prejudice or disclaimer, and amend 3 with the subject matter of allowable claim 2 with prejudice or disclaimer as to its original subject matter. A complete listing of all pending claims is presented.

1. (Cancelled)

2. (Amended) A solid-state image pickup device having:

unit pixels arranged in a matrix form, each pixel unit comprising a photoelectrical conversion element, a transfer transistor for transferring a signal of said photoelectrical conversion element to a floating node, an amplifying transistor for outputting a signal of said floating node to a signal line, a reset transistor for resetting said floating node, and a P-type MOS transistor, wherein said P-type MOS transistor is connected between a wire to which a main electrode of said reset transistor at the opposite side to said floating node is connected and a driving circuit for selectively applying a reset voltage to said wire [The solid-state image pickup device as claimed in claim 1], wherein the channel voltage of said P-type MOS transistor is equal to 0.4V to 0.7V.

3. (Amended) A camera system comprising:

a solid-state image pickup device in which a unit pixel has a photoelectrical conversion element, a transfer transistor for transferring a signal of said photoelectrical conversion element to a floating node, an amplifying transistor for outputting a signal of said floating node to a signal line, a reset transistor for resetting said floating node, a P-type MOS transistor, an optical system for guiding incident light to said image pickup portion of said solid-state image pickup device; and a signal processing circuit for processing the output

signal of said solid-state image pickup device, wherein said P-type MOS transistor, is connected between a wire to which a main electrode of said reset transistor at the opposite side to said floating node is connected and a driving circuit for selectively applying a reset voltage to said wire, and wherein the channel voltage of said P-type MOS transistor is equal to 0.4V to 0.7V.